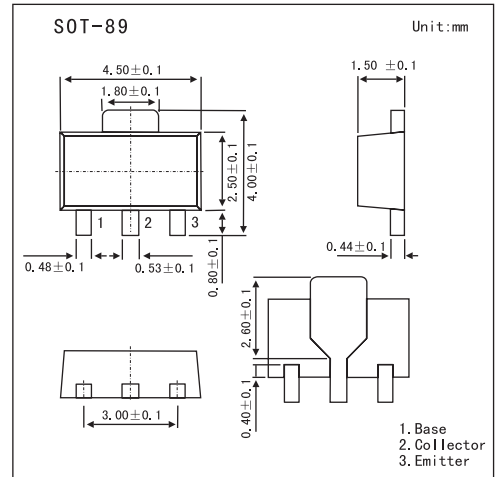


2SD1622

■ Features

- Adoption of FBET process..
- Very small size making it easy to provide highdensity hybrid ICs.



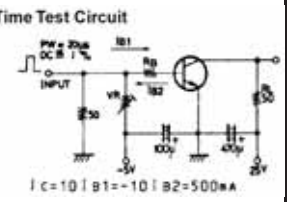
■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	1	A
Collector current (pulse)	I _{CP}	2	A
Collector dissipation	P _C	500	mW
	P _C *	1.3	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Mounted on ceramic board(250mm2X0.8mm)

2SD1622

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Collector cutoff current	IcBO	V _{CB} = 50 V, I _E =0			100	nA	
Emitter cutoff current	I _{EBO}	V _{EB} = 4 V, I _C =0			100	nA	
DC current gain	h _{FE}	V _{CE} = 2 V, I _C = 100 mA	100		560		
Gain bandwidth product	f _T	V _{CE} = 10 V, I _C = 50 mA		150		MHz	
Output capacitance	C _{ob}	V _{CB} = 10 V, f = 1.0MHz		8.5		pF	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 500 mA, I _B = 50 mA		120	300	mV	
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 500 mA, I _B = 50 mA		0.9	1.2	V	
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	60			V	
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	50			V	
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	5			V	
Turn-on timie	ton	Switching Time Test Circuit 		40		ns	
Storage time	tstg				350		ns
Turn-off time	tf				30		ns

■ hFE Classification

Marking	DE			
	R	S	T	U
hFE	100~200	140~280	200~400	280~560